
Oral presentation | 13. Semiconductors A (Silicon) | 13.2 Insulator technology

[19a-A17-1~12]13.2 Insulator technology

Fri. Sep 19, 2014 9:00 AM - 12:30 PM A17 (E308)

△ : Young Scientist Oral Presentation Award Applied

▲ : English Presentation

▼ : Both Award Applied and English Presentation

10:30 AM - 11:00 AM

[19a-A17-6][JSAP Paper Award Speech] (30min.)

Chemical Structure of Interfacial Transition Layer Formed on Si(100) and Its Dependence on Oxidation Temperature, Annealing in Forming Gas, and Difference in Oxidizing Species

[○]Tomoyuki Suwa¹, Akinobu Teramoto¹, Yuki Kumagai¹, Kenichi Abe¹, Xiang Li¹, Yukihiro Nakao¹, Masashi Yamamoto², Hiroshi Nohira³, Takayuki Muro⁴, Toyohiko Kinoshita⁴, Shigetoshi Sugawa¹, Tadahiro Ohmi¹, Takeo Hattori¹ (Tohoku University¹, Stella Chemifa², Tokyo City University³, JASRI⁴)